

WP3DPD1C Photodiode

DESCRIPTION

- Made with PIN silicon phototransistor chips

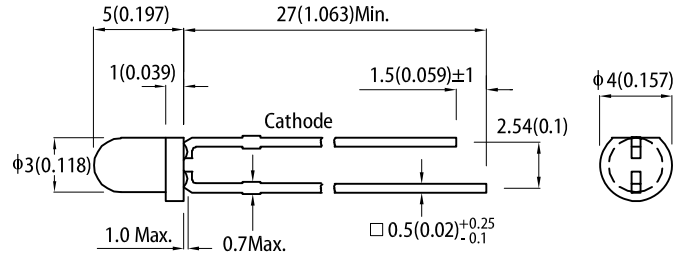
FEATURES

- Mechanically and spectrally matched to the infrared emitting LED lamp
- RoHS compliant

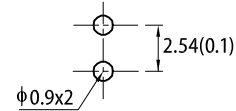
APPLICATIONS

- Infrared applied systems
- Optoelectronic switches
- Photodetector control circuits
- Sensor technology

PACKAGE DIMENSIONS



Recommended PCB Layout



Notes:

- All dimensions are in millimeters (inches).
- Tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
- Lead spacing is measured where the leads emerge from the package.
- The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.

ABSOLUTE MAXIMUM RATINGS at $T_A=25^\circ\text{C}$

Parameter	Max.Ratings	Units
Power Dissipation	150	mW
Operating Temperature	-40 to +85	$^\circ\text{C}$
Storage Temperature	-40 to +85	$^\circ\text{C}$
Lead Solder Temperature ^[1]	260 $^\circ\text{C}$ For 3 Seconds	
Lead Solder Temperature ^[2]	260 $^\circ\text{C}$ For 5 Seconds	

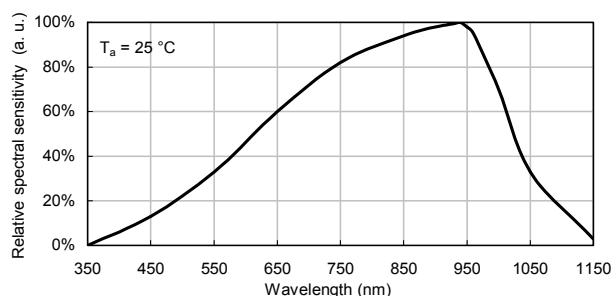
Notes:
 1. 2mm below package base.
 2. 5mm below package base.
 3. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

ELECTRICAL / OPTICAL CHARACTERISTICS at $T_A=25^\circ\text{C}$

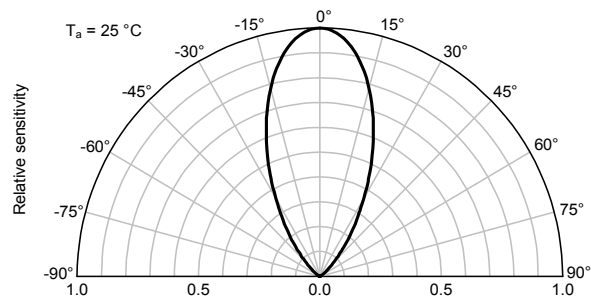
Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Reverse Break down Voltage	$V_{(BR)R}$	33	170	-	V	$I_R = 100\mu\text{A}$ $H = 0\text{mW/cm}^2$
Reverse Dark Current	$I_{D(R)}$	-	-	10	nA	$V_R = 10\text{V}$ $H = 0\text{mW/cm}^2$
Open Circuit Voltage	V_{OC}	-	390	-	mV	$\lambda = 940\text{nm}$ $H = 5\text{mW/cm}^2$
Rise Time	T_R	-	6	-	nS	$V_R = 10\text{V}$ $\lambda = 940\text{nm}$ $R_L = 1000\Omega$
Fall Time	T_F	-	6	-	nS	
Light current	I_S	0.07	0.16	-	μA	$V_R = 5\text{V}$ $E_e = 0.08\text{mW/cm}^2$ $\lambda = 940\text{nm}$
Total Capacitance	C_T	-	5	-	pF	$V_R = 10\text{V}$ $F = 1\text{MHz}$ $H = 0\text{mW/cm}^2$
Range of spectral bandwidth	$\lambda_{0.1}$	420	-	1120	nm	-
Wavelength of peak sensitivity	λ_p	-	940	-	nm	-
Angle of half sensitivity	$2\theta_{1/2}$	-	50	-	deg	-

TECHNICAL DATA

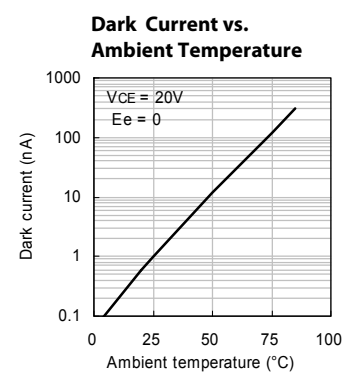
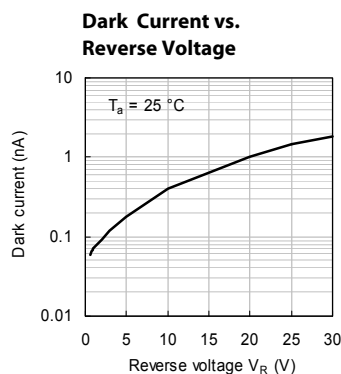
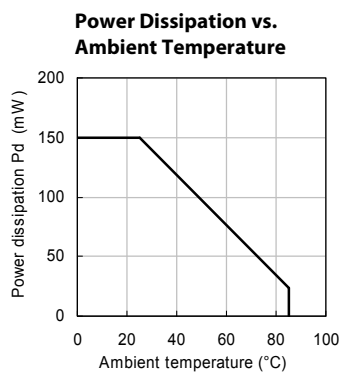
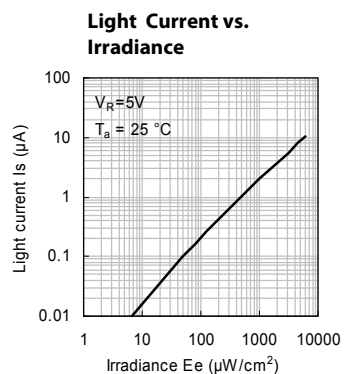
RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH



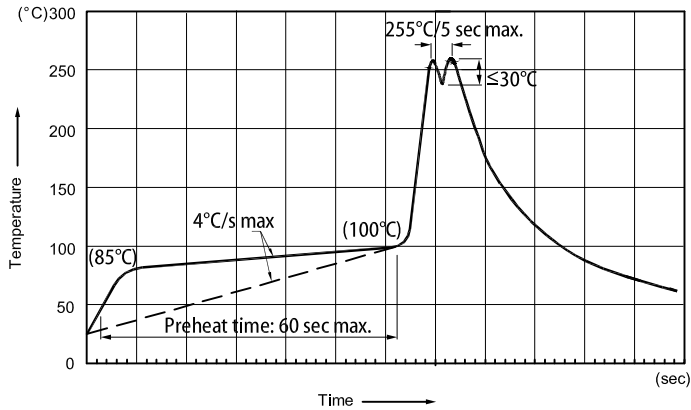
RELATIVE RADIANT SENSITIVITY vs. ANGULAR DISPLACEMENT



PHOTODIODE



RECOMMENDED WAVE SOLDERING PROFILE



Notes:

1. Recommend pre-heat temperature of 105°C or less (as measured with a thermocouple attached to the LED pins) prior to immersion in the solder wave with a maximum solder bath temperature of 260°C
2. Peak wave soldering temperature between 245°C ~ 255°C for 3 sec (5 sec max).
3. Do not apply stress to the epoxy resin while the temperature is above 85°C.
4. Fixtures should not incur stress on the component when mounting and during soldering process.
5. SAC 305 solder alloy is recommended.
6. No more than one wave soldering pass.

PACKING & LABEL SPECIFICATIONS

